

ABSTRACT OF THE DISCLOSURE

SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

The semiconductor device of the invention includes a capacitor device, which is formed on a substrate and which includes a capacitive lower electrode, a capacitive insulating film made of an insulating metal oxide film and a capacitive upper electrode. An interlevel insulating film having an opening reaching the capacitive upper electrode is formed over the capacitor device. A metal interconnection including a titanium film is formed over the interlevel insulating film so as to be electrically connected to the capacitive upper electrode through the opening. An anti-diffusion film having conductivity is formed between the capacitive upper electrode and the metal interconnection for preventing titanium atoms composing the titanium film of the metal interconnection from passing through the capacitive upper electrode and diffusing into the capacitive insulating film.

Figure 1.